IN THE CLAIMS:

1. (Currently amended) A film laminate comprising a heat-resistant polymer film, a plasma CVD layer formed by decompsition of an organic metal compound through application of a plasma CVD to the heat-resistant polymer film, said plasma CVD layer being provided on at least one side of said heat-resistant polymer film, and an electrically conductive layer provided on said plasma CVD layer.

2. (Original) The film laminate as recited in claim 1, wherein said organic metal compound includes at least one member selected from the group consisting of organic silicon compounds, organic titanium compounds and organic aluminum compounds.

3. (Previously presented) The film laminate as recited in claim 1, wherein said heat-resistant polymer film is at least one member selected from the group consisting of aromatic polyimide films, liquid crystal polyester films and aromatic polyamide films.

4. (Previously presented) The film laminate as recited in claim 1, wherein said heat-resistant polymer film is an aromatic polyimide film having a water absorption coefficient of 2 % or less and a linear expansion coefficient of $2'10^{-5}$/°C or less.

5. (Previously presented) The film laminate as recited in claim 1, additionally comprising a resin layer which has a thickness of 5 μm or less, which is provided between said heat-resistant polymer layer and said plasma CVD layer and which contains a fluorinated polyimide resin or a silicone-polyimide resin.

6. (Previously presented) The film laminate as recited in claim 1, wherein said electrically conductive layer is a copper layer formed by a sputtering method and having a thickness of 1 μm or less.

7. (Currently amended) The film laminate as recited in claim 1, wherein said electrically conductive layer is a two-layered copper layer having a total thickness of 20 μm or less and composed of a copper layer formed by a sputtering method and

an electrolytic copper layer formed by ~~an~~ electrolytic plating using said copper layer as an electrode.

8. (Previously presented) A flexible circuit board comprising a film laminate according to claim 1 with said electrically conductive layer being patterned to form a circuit, and a copper plating layer provided on said circuit.

9. (Currently amended) A flexible circuit board produced ~~obtainable~~ by a method comprising forming a photosensitive resin over said electrically conductive layer of a film laminate according to claim 1, patterning said photosensitive layer to expose said electrically conductive layer, copper-plating said exposed electrically conductive layer to form a copper layer, and removing remaining photosensitive resin and said electrically conductive layer below said remaining photosensitive resin.

10. (New) The film laminate as recited in claim 1, wherein said plasma CVD layer has a thickness of 0.01 to 1 μm.

11. (New) The film laminate as recited in claim 1, wherein said organic metal compound is an organic silicon compound.

12. (New) The film laminate as recited in claim 11, wherein the plasma CVD layer is silicon oxide.

13. (New) The film laminate as recited in claim 1, wherein said organic metal compound is an organic titanium compound.

14. (New) The film laminate as recited in claim 1, wherein said organic metal compound is an organic aluminum compound.

15. (New) A method of preparing a film laminate, comprising the steps of:

placing a heat-resistant polymer film in a vacuum chamber containing a gas comprising an organic metal compound,

subjecting said gas to a glow discharge to decompose the organic metal

compound and to deposit a plasma CVD layer on the heat-resistant polymer film, and

forming an electrically conductive layer on said plasma CVD layer.